### 400MHz to 2.5GHz, Low-Noise, SiGe Downconverter Mixers

#### **General Description**

The MAX2680/MAX2681/MAX2682 miniature, low-cost, low-noise downconverter mixers are designed for lowvoltage operation and are ideal for use in portable communications equipment. Signals at the RF input port are mixed with signals at the local oscillator (LO) port using a double-balanced mixer. These downconverter mixers operate with RF input frequencies between 400MHz and 2500MHz, and downconvert to IF output frequencies between 10MHz and 500MHz.

The MAX2680/MAX2681/MAX2682 operate from a single +2.7V to +5.5V supply, allowing them to be powered directly from a 3-cell NiCd or a 1-cell Lithium battery. These devices offer a wide range of supply currents and input intercept (IIP3) levels to optimize system performance. Additionally, each device features a low-power shutdown mode in which it typically draws less than 0.1µA of supply current. Consult the *Selector Guide* for various combinations of IIP3 and supply current.

The MAX2680/MAX2681/MAX2682 are manufactured on a high-frequency, low-noise, advanced silicon-germanium process and are offered in the space-saving 6-pin SOT23 package.

#### **Applications**

- 400MHz/900MHz/2.4GHz ISM-Band Radios
- Personal Communications Systems (PCS)
- Cellular and Cordless Phones
- Wireless Local Loop
- IEEE-802.11 and Wireless Data

#### **Selector Guide**

#### FREQUENCY 900MHz 1950MHz 2450MHz lcc PART (mA) IIP3 NF GAIN IIP3 NF GAIN IIP3 NF GAIN (dB) (dB) (dBm) (dB) (dB) (dBm) (dB) (dBm) (dB) MAX2680 5.0 -12.9 6.3 11.6 -8.2 8.3 7.6 -6.9 11.7 7.0 MAX2681 8.7 -6.1 7.0 14.2 11.1 8.4 +1.0 12.7 7.7 +0.5 MAX2682 15.0 -1.8 6.5 14.7 +4.4 10.2 10.4 +3.2 13.4 7.9

Typical Operating Circuit appears at end of data sheet.



#### Features

- 400MHz to 2.5GHz Operation
- +2.7V to +5.5V Single-Supply Operation
- Low Noise Figure: 6.3dB at 900MHz (MAX2680)
- High Input Third-Order Intercept Point (IIP3 at 2450MHz)
  - -6.9dBm at 5.0mA (MAX2680)
  - +1.0dBm at 8.7mA (MAX2681)
  - +3.2dBm at 15.0mA (MAX2682)
- < 0.1µA Low-Power Shutdown Mode
- Ultra-Small Surface-Mount Packaging

#### **Ordering Information**

PART	ART TEMP RANGE		SOT TOP MARK	
MAX2680EUT-T	-40°C to +85°C	6 SOT23	AAAR	
MAX2681EUT-T	-40°C to +85°C	6 SOT23	AAAS	
MAX2682EUT-T	-40°C to +85°C	6 SOT23	AAAT	

### 400MHz to 2.5GHz, Low-Noise, SiGe Downconverter Mixers

#### **Absolute Maximum Ratings**

V <sub>CC</sub> to GND	0.3V to +6.0V
RFIN Input Power (50Ω source)	
LO Input Power (50Ω source)	+10dBm
SHDN, IFOUT, RFIN to GND	0.3V to (V <sub>CC</sub> + 0.3V)
LO to GND	$(V_{CC} - 1V)$ to $(V_{CC} + 0.3V)$

Continuous Power Dissipation ( $T_A = +70^{\circ}C$ )	
SOT23 (derate 8.7mW/°C above +70°C)	696mW
Operating Temperature Range	40°C to +85°C
Junction Temperature	+150°C
Storage Temperature Range	-65°C to +160°C
Lead Temperature (soldering, 10s)	+300°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

CAUTION! ESD SENSITIVE DEVICE

### **DC Electrical Characteristics**

 $(V_{CC} = +2.7V \text{ to } +5.5V, \overline{SHDN} = +2V, T_A = T_{MIN} \text{ to } T_{MAX} \text{ unless otherwise noted. Typical values are at } V_{CC} = +3V \text{ and } T_A = +25^{\circ}C.$ Minimum and maximum values are guaranteed over temperature by design and characterization.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
		MAX2680		5.0	7.7	
Operating Supply Current	ICC	MAX2681		8.7	12.7	mA
		MAX2682		15.0	21.8	
Shutdown Supply Current	I <sub>CC</sub>	<u>SHDN</u> = 0.5V		0.05		μA
Shutdown Input Voltage High	VIH		2.0			V
Shutdown Input Voltage Low	VIL				0.5	V
Shutdown Input Bias Current	ISHDN	0 < SHDN < V <sub>CC</sub>		0.2		μA

#### **AC Electrical Characteristics**

(MAX2680/1/2 EV Kit, V<sub>CC</sub> =  $\overline{SHDN}$  = +3.0V, T<sub>A</sub> = +25°C, unless otherwise noted. RFIN and IFOUT matched to 50 $\Omega$ . P<sub>LO</sub> = -5dBm, P<sub>RFIN</sub> = -25dBm.)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
MAX2680						
RF Frequency Range	(Notes 1, 2)	400		2500	MHz	
LO Frequency Range	(Notes 1, 2)	400		2500	MHz	
IF Frequency Range	(Notes 1, 2)	10		500	MHz	
	f <sub>RF</sub> = 400MHz, f <sub>LO</sub> = 445MHz, f <sub>IF</sub> = 45MHz		7.3			
Conversion Dower Coin	f <sub>RF</sub> = 900MHz, f <sub>LO</sub> = 970MHz, f <sub>IF</sub> = 70MHz		11.6			
Conversion Power Gain	f <sub>RF</sub> = 1950MHz, f <sub>LO</sub> = 1880MHz, f <sub>IF</sub> = 70MHz (Note 1)	5.7	7.6	8.6	dB	
	f <sub>RF</sub> = 2450MHz, f <sub>LO</sub> = 2210MHz, f <sub>IF</sub> = 240MHz		7.0			
Gain Variation Over Temperature	$f_{RF}$ = 1950MHz, $f_{LO}$ = 1880MHz, $f_{IF}$ = 70MHz, $T_A$ = $T_{MIN}$ to $T_{MAX}$ (Note 1)		1.9	2.4	dB	
	f <sub>RF</sub> = 900MHz, 901MHz, f <sub>LO</sub> = 970MHz, f <sub>IF</sub> = 70MHz		-12.9			
Input Third-Order Intercept Point (Note 3)	f <sub>RF</sub> = 1950MHz, 1951MHz, f <sub>LO</sub> = 1880MHz, f <sub>IF</sub> = 70MHz		-8.2		dBm	
(Note 3)	f <sub>RF</sub> = 2450MHz, 2451MHz, f <sub>LO</sub> = 2210MHz, f <sub>IF</sub> = 240MHz		-6.9			
	f <sub>RF</sub> = 900MHz, f <sub>LO</sub> = 970MHz, f <sub>IF</sub> = 70MHz		6.3			
Noise Figure (Single Sideband)	f <sub>RF</sub> = 1950MHz, f <sub>LO</sub> = 2020MHz, f <sub>IF</sub> = 70MHz		8.3		dB	
	f <sub>RF</sub> = 2450MHz, f <sub>LO</sub> = 2210MHz, f <sub>IF</sub> = 240MHz		11.7			
LO Input VSWR	50Ω source impedance		1.5:1			
LO Leakage at IFOUT Port	f <sub>LO</sub> = 1880MHz		-22		dBm	

### 400MHz to 2.5GHz, Low-Noise, SiGe Downconverter Mixers

### **AC Electrical Characteristics (continued)**

(MAX2680/1/2 EV Kit,  $V_{CC} = \overline{SHDN} = +3.0V$ ,  $T_A = +25^{\circ}C$ , unless otherwise noted. RFIN and IFOUT matched to  $50\Omega$ .  $P_{LO} = -5dBm$ ,  $P_{RFIN} = -25dBm$ .)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS				
LO Leakage at RFIN Port	f <sub>LO</sub> = 1880MHz		-26		dBm				
IF/2 Spurious Response	f <sub>RF</sub> = 1915MHz, f <sub>LO</sub> = 1880MHz, f <sub>IF</sub> = 70MHz (Note 4)		-51		dBm				
MAX2681									
RF Frequency Range	(Notes 1, 2)	400		2500	MHz				
LO Frequency Range	(Notes 1, 2)	400		2500	MHz				
IF Frequency Range	(Notes 1, 2)	10		500	MHz				
	f <sub>RF</sub> = 400MHz, f <sub>LO</sub> = 445MHz, f <sub>IF</sub> = 45MHz		11.0		1				
	f <sub>RF</sub> = 900MHz, f <sub>LO</sub> = 970MHz, f <sub>IF</sub> = 70MHz		14.2						
Conversion Power Gain	f <sub>RF</sub> = 1950MHz, f <sub>LO</sub> = 1880MHz, f <sub>IF</sub> = 70MHz (Note 1)	6.7	8.4	9.4	dB				
	f <sub>RF</sub> = 2450MHz, f <sub>LO</sub> = 2210MHz, f <sub>IF</sub> = 240MHz		7.7						
Gain Variation Over Temperature	$f_{RF}$ = 1950MHz, $f_{LO}$ = 1880MHz, $f_{IF}$ = 70MHz, $T_A$ = $T_{MIN}$ to $T_{MAX}$ (Note 1)		1.7	2.3	dB				
	f <sub>RF</sub> = 900MHz, 901MHz, f <sub>LO</sub> = 970MHz, f <sub>IF</sub> = 70MHz		-6.1						
Input Third-Order Intercept Point	f <sub>RF</sub> = 1950MHz, 1951MHz, f <sub>LO</sub> = 1880MHz, f <sub>IF</sub> = 70MHz		+0.5		dBm				
(Note 3)	f <sub>RF</sub> = 2450MHz, 2451MHz, f <sub>LO</sub> = 2210MHz, f <sub>IF</sub> = 240MHz		+1.0		1				
	f <sub>RF</sub> = 900MHz, f <sub>LO</sub> = 970MHz, f <sub>IF</sub> = 70MHz	7.0							
Noise Figure (Single Sideband)	f <sub>RF</sub> = 1950MHz, f <sub>LO</sub> = 2020MHz, f <sub>IF</sub> = 70MHz		11.1		dB				
	f <sub>RF</sub> = 2450MHz, f <sub>LO</sub> = 2210MHz, f <sub>IF</sub> = 240MHz		12.7						
LO Input VSWR	50Ω source impedance		1.5:1						
LO Leakage at IFOUT Port	f <sub>LO</sub> = 1880MHz		-23		dBm				
LO Leakage at RFIN Port	f <sub>LO</sub> = 1880MHz		-27		dBm				
IF/2 Spurious Response	f <sub>RF</sub> = 1915MHz, f <sub>LO</sub> = 1880MHz, f <sub>IF</sub> = 70MHz (Note 4)		-65		dBm				
MAX2682									
RF Frequency Range	(Notes 1, 2)	400		2500	MHz				
LO Frequency Range	(Notes 1, 2)	400		2500	MHz				
IF Frequency Range	(Notes 1, 2)	10		500	MHz				
	f <sub>RF</sub> = 400MHz, f <sub>LO</sub> = 445MHz, f <sub>IF</sub> = 45MHz		13.4						
	f <sub>RF</sub> = 900MHz, f <sub>LO</sub> = 970MHz, f <sub>IF</sub> = 70MHz		14.7						
Conversion Power Gain	f <sub>RF</sub> = 1950MHz, f <sub>LO</sub> = 1880MHz, f <sub>IF</sub> = 70MHz (Note 1)	8.7	10.4	11.7	dB				
	f <sub>RF</sub> = 2450MHz, f <sub>LO</sub> = 2210MHz, f <sub>IF</sub> = 240MHz		7.9						
Gain Variation Over Temperature	$f_{RF}$ = 1950MHz, $f_{LO}$ = 1880MHz, $f_{IF}$ = 70MHz, T <sub>A</sub> = T <sub>MIN</sub> to T <sub>MAX</sub> (Note 1)		2.1	3.2	dB				
	f <sub>RF</sub> = 900MHz, 901MHz, f <sub>LO</sub> = 970MHz, f <sub>IF</sub> = 70MHz -1.8								
Input Third-Order Intercept Point	f <sub>RF</sub> = 1950MHz, 1951MHz, f <sub>LO</sub> = 1880MHz, f <sub>IF</sub> = 70MHz		+4.4		dBm				
(Note 3)	f <sub>RF</sub> = 2450MHz, 2451MHz, f <sub>LO</sub> = 2210MHz, f <sub>IF</sub> = 240MHz		+3.2		1				
	f <sub>RF</sub> = 900MHz, f <sub>LO</sub> = 970MHz, f <sub>IF</sub> = 70MHz								
Noise Figure (Single Sideband)	f <sub>RF</sub> = 1950MHz, f <sub>LO</sub> = 2020MHz, f <sub>IF</sub> = 70MHz		10.2		dB				
/	f <sub>RF</sub> = 2450MHz, f <sub>LO</sub> = 2210MHz, f <sub>IF</sub> = 240MHz		13.4						

### 400MHz to 2.5GHz, Low-Noise, SiGe Downconverter Mixers

### **AC Electrical Characteristics (continued)**

(MAX2680/1/2 EV Kit,  $V_{CC} = \overline{SHDN} = +3.0V$ ,  $T_A = +25^{\circ}C$ , unless otherwise noted. RFIN and IFOUT matched to  $50\Omega$ .  $P_{LO} = -5dBm$ ,  $P_{RFIN} = -25dBm$ .)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
LO Input VSWR	50Ω source impedance		1.5:1		
LO Leakage at IFOUT Port	f <sub>LO</sub> = 1880MHz		-23		dBm
LO Leakage at RFIN Port	f <sub>LO</sub> = 1880MHz		-27		dBm
IF/2 Spurious Response	f <sub>RF</sub> = 1915MHz, f <sub>LO</sub> = 1880MHz, f <sub>IF</sub> = 70MHz (Note 4)		-61		dBm

Note 1: Guaranteed by design and characterization.

Note 2: Operation outside of this specification is possible, but performance is not characterized and is not guaranteed.

Note 3: Two input tones at -25dBm per tone.

**Note 4:** This spurious response is caused by a higher-order mixing product (2x2). Specified RF frequency is applied and IF output power is observed at the desired IF frequency (70MHz).

### **Typical Operating Characteristics**



### 400MHz to 2.5GHz, Low-Noise, SiGe Downconverter Mixers

#### **Typical Operating Characteristics (continued)**



### 400MHz to 2.5GHz, Low-Noise, SiGe Downconverter Mixers

#### **Typical Operating Characteristics (continued)**



### 400MHz to 2.5GHz, Low-Noise, SiGe Downconverter Mixers

#### **Typical Operating Characteristics (continued)**



## 400MHz to 2.5GHz, Low-Noise, SiGe Downconverter Mixers

### **Typical Operating Characteristics (continued)**

(*Typical Operating Circuit*,  $V_{CC} = \overline{SHDN} = +3.0V$ ,  $P_{RFIN} = -25dBm$ ,  $P_{LO} = -5dBm$ ,  $T_A = +25^{\circ}C$ , unless otherwise noted.)



#### **Pin Configuration**



### **Pin Description**

PIN	NAME	FUNCTION
1	LO	Local-Oscillator Input. Apply a local-oscillator signal with an amplitude of -10dBm to 0 (50 $\Omega$ source). AC-couple this pin to the oscillator with a DC-blocking capacitor. Nominal DC voltage is V <sub>CC</sub> - 0.4V.
2	GND	Mixer Ground. Connect to the ground plane with a low-inductance connection.
3	RFIN	Radio Frequency Input. AC-couple to this pin with a DC-blocking capacitor. Nominal DC voltage is 1.5V. See the <i>Applications Information</i> section for details on impedance matching.
4	IFOUT	Intermediate Frequency Output. Open-collector output requires an inductor to $V_{CC}$ . AC-couple to this pin with a DC-blocking capacitor. See the <i>Applications Information</i> section for details on impedance matching.
5	V <sub>CC</sub>	Supply Voltage Input, +2.7V to +5.5V. Bypass with a capacitor to the ground plane. Capacitor value depends upon desired operating frequency.
6	SHDN	Active-Low Shutdown. Drive low to disable all device functions and reduce the supply current to less than $5\mu$ A. For normal operation, drive high or connect to V <sub>CC</sub> .

#### **Detailed Description**

The MAX2680/MAX2681/MAX2682 are 400MHz to 2.5GHz, silicon-germanium, double-balanced downconverter mixers. They are designed to provide optimum linearity performance for a specified supply current. They consist of a double-balanced Gilbert-cell mixer with single-ended RF, LO, and IF port connections. An on-chip bias cell provides a low-power shutdown feature. Consult the <u>Selector Guide</u> for device features and comparison.

#### **Applications Information**

#### Local-Oscillator (LO) Input

The LO input is a single-ended broadband port with a typical input VSWR of better than 2.0:1 from 400MHz to 2.5GHz. The LO signal is mixed with the RF input signal, and the resulting downconverted output appears at IFOUT. AC-couple LO with a capacitor. Drive the LO port with a signal ranging from -10dBm to 0 ( $50\Omega$  source).

#### **RF Input**

The RF input frequency range is 400MHz to 2.5GHz. The RF input requires an impedance-matching network as well as a DC-blocking capacitor that can be part of the matching network. Consult Tables 1 and 2, as well as the RF Port Impedance vs. RF Frequency graph in the *Typical Operating Characteristics* section for information on matching.

### 400MHz to 2.5GHz, Low-Noise, SiGe Downconverter Mixers

#### **IF Output**

The IF output frequency range extends from 10MHz to 500MHz. IFOUT is a high-impedance, open-collector output that requires an external inductor to  $V_{CC}$  for proper biasing. For optimum performance, the IF port requires an impedance-matching network. The configuration and values for the matching network is dependent upon the frequency and desired output impedance. For assistance in choosing components for optimal performance, see <u>Table 3</u> and <u>Table 4</u> as well as the IF Port Impedance vs. IF Frequency graph in the *Typical Operating Characteristics* section.

#### Power-Supply and SHDN Bypassing

Proper attention to voltage supply bypassing is essential for high-frequency RF circuit stability. Bypass  $V_{CC}$  with a 10µF capacitor in parallel with a 1000pF capacitor. Use separate vias to the ground plane for each of the bypass capacitors and minimize trace length to reduce inductance. Use separate vias to the ground plane for each ground pin. Use low-inductance ground connections.

Decouple  $\overline{SHDN}$  with a 1000pF capacitor to ground to minimize noise on the internal bias cell. Use a series resistor (typically 100 $\Omega$ ) to reduce coupling of high-frequency signals into the  $\overline{SHDN}$  pin.

#### Layout Issues

A well-designed PC board is an essential part of an RF circuit. For best performance, pay attention to powersupply issues as well as to the layout of the RFIN and IFOUT impedance-matching network.

Table	÷.,		on	impedance	
				FREQUENCY	

Table 1 PEIN Port Impedance

PART	FREQUENCY						
FARI	400MHz	900MHz	1950MHz	2450MHz			
MAX2680	179-j356	54-j179	32-j94	33-j73			
MAX2681	209-j332	75-j188	34-j108	33-j86			
MAX2682	206-j306	78-j182	34-j106	29-j86			

#### Table 2. RF Input Impedance-Matching Component Values

						FREQU	JENCY					
MATCHING	MAX2680				MAX2681			MAX2682				
COMPONENTS	400	900	1950	2450	400	900	1950	2450	400	900	1950	2450
	MHz	MHz	MHz	MHz	MHz	MHz	MHz	MHz	MHz	MHz	MHz	MHz
Z1	86nH	270pF	1.5pF	Short	68nH	270pF	1.5pF	Short	68nH	1.5pF	Short	Short
Z2	270pF	22nH	270pF	270pF	270pF	18nH	270pF	270pF	270pF	270pF	270pF	270pF
Z3	Open	Open	1.8nH	1.8nH	0.5pF	Open	1.8nH	2.2nH	0.5pF	10nH	2.2nH	1.2nH

Note: Z1, Z2, and Z3 are found in the Typical Operating Circuit.

PART	FREQUENCY						
FARI	45MHz	70MHz	240MHz				
MAX2680	960-j372	803-j785	186-j397				
MAX2681	934-j373	746-j526	161-j375				
MAX2682	670-j216	578-j299	175-j296				

#### **Table 3. IFOUT Port Impedance**

# Table 4. IF Output Impedance-MatchingComponents

MATCHING	FREQUENCY				
COMPONENT	45MHz	70MHz	240MHz		
L1	390nH	330nH	82nH		
C2	39pF	15pF	3pF		
R1	250Ω	Open	Open		

### 400MHz to 2.5GHz, Low-Noise, SiGe Downconverter Mixers

#### **Power-Supply Layout**

To minimize coupling between different sections of the IC, the ideal power-supply layout is a star configuration with a large decoupling capacitor at a central V<sub>CC</sub> node. The V<sub>CC</sub> traces branch out from this central node, each going to a separate V<sub>CC</sub> node on the PC board. At the end of each trace is a bypass capacitor that has low ESR at the RF frequency of operation. This arrangement provides local decoupling at the V<sub>CC</sub> pin. At high frequencies, any signal leaking out of one supply pin sees a relatively high impedance (formed by the V<sub>CC</sub> trace inductance) to the central V<sub>CC</sub> node, and an even higher impedance to any other supply pin, as well as a low impedance to ground through the bypass capacitor.

#### Impedance-Matching Network Layout

The RFIN and IFOUT impedance-matching networks are very sensitive to layout-related parasitics. To minimize parasitic inductance, keep all traces short and place components as close as possible to the chip. To minimize parasitic capacitance, use cutouts in the ground plane (and any other plane) below the matching network components. However, avoid cutouts that are larger than necessary since they act as aperture antennas.





## 400MHz to 2.5GHz, Low-Noise, SiGe Downconverter Mixers

#### **Package Information**

For the latest package outline information and land patterns (footprints), go to <u>www.maximintegrated.com/packages</u>. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.



## 400MHz to 2.5GHz, Low-Noise, SiGe Downconverter Mixers

#### **Package Information (continued)**

For the latest package outline information and land patterns (footprints), go to <u>www.maximintegrated.com/packages</u>. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

NЦ	TES:	SYMBOL	MIN 0.90	NOMINAL	MAX 1,45
1.	ALL DIMENSIONS ARE IN MILLIMETERS.	A1	0.00	0.05	0.15
$\triangle$	FRET LENGTH MEASURED AT INTERCERT REINE REIN/CEN DATING A A	A2	0,90	1.10	1.30
<u>/2'/</u>	FODT LENGTH MEASURED AT INTERCEPT POINT BETWEEN DATUM A & LEAD SURFACE.	b	0.35	0.40	0.50
		С	0.08	0.15	0.20
З.	PACKAGE DUTLINE EXCLUSIVE OF MOLD FLASH & METAL BURR, MOLD	D	2.80	2.90	3.00
FLASH, PRUIRUSIUN DR M	FLASH, PROTRUSION OR METAL BURR SHOULD NOT EXCEED 0.25mm.	E E	<u>2.60</u> 1.50	2.80	<u>3.00</u> 1.75
4.	PACKAGE DUTLINE INCLUSIVE DF SDLDER PLATING.	E1	0.35	0,45	0.60
			0.00	0.60 REF.	0.00
5. PIN 1 IS LOWER LEFT PIN WHEN READING TOP MARK FROM LEFT TO		e1	1.90 BSC.		
RIGHT, (SEE EXAMPLE TOP )	KIUHI, (SEE EXAMPLE IUP MAKK)	e		0.95 BSC.	
6.	PIN 1 I.D. DOT IS 0.3mm Ø MIN. LOCATED ABO∨E PIN 1.	۵	0°	2.5*	10°
	MEETS JEDEC MO178, VARIATION AB. SOLDER THICKNESS MEASURED AT FLAT SECTION OF LEAD BETWEEN	U6SN-1,	16-2, U6-4, U6CN-2, , U6F-6, U6FH-6; U6FH-7		
	0.08mm AND 0.15mm FROM LEADTIP.	** U6FH-7	TO BE US	ED FOR NP42	PARTS DNLY.
9.	LEAD TO BE COPLANAR WITHIN 0.1mm.				
	LEAD TO BE COPLANAR WITHIN 0.1mm. NUMBER OF LEADS SHOWN ARE FOR REFERENCE ONLY.				
10.					
10. 11.	NUMBER OF LEADS SHOWN ARE FOR REFERENCE ONLY.				
10. 11.	NUMBER OF LEADS SHOWN ARE FOR REFERENCE ONLY. MARKING IS FOR PACKAGE ORIENTATION REFERENCE ONLY. ALL DIMENSIONS APPLY TO BOTH LEADED (-) AND P6FREE (+) PKG.				
10. 11.	NUMBER OF LEADS SHOWN ARE FOR REFERENCE ONLY. MARKING IS FOR PACKAGE ORIENTATION REFERENCE ONLY. ALL DIMENSIONS APPLY TO BOTH LEADED (-) AND P6FREE (+) PKG.				
10. 11.	NUMBER OF LEADS SHOWN ARE FOR REFERENCE ONLY. MARKING IS FOR PACKAGE ORIENTATION REFERENCE ONLY. ALL DIMENSIONS APPLY TO BOTH LEADED (-) AND P6FREE (+) PKG.			maxim	
10. 11.	NUMBER OF LEADS SHOWN ARE FOR REFERENCE ONLY. MARKING IS FOR PACKAGE ORIENTATION REFERENCE ONLY. ALL DIMENSIONS APPLY TO BOTH LEADED (-) AND P6FREE (+) PKG.			maxim	:d.
10. 11.	NUMBER OF LEADS SHOWN ARE FOR REFERENCE ONLY. MARKING IS FOR PACKAGE ORIENTATION REFERENCE ONLY. ALL DIMENSIONS APPLY TO BOTH LEADED (-) AND P6FREE (+) PKG.	ΠΠ.Ε:		integrate	
10. 11.	NUMBER OF LEADS SHOWN ARE FOR REFERENCE ONLY. MARKING IS FOR PACKAGE ORIENTATION REFERENCE ONLY. ALL DIMENSIONS APPLY TO BOTH LEADED (-) AND P6FREE (+) PKG.			maxim integrate _INE, SOT	
10. 11. 12.	NUMBER OF LEADS SHOWN ARE FOR REFERENCE ONLY. MARKING IS FOR PACKAGE ORIENTATION REFERENCE ONLY. ALL DIMENSIONS APPLY TO BOTH LEADED (-) AND P6FREE (+) PKG.		GE DUTI	integrate	6L BDDY

For pricing, delivery, and ordering information, please contact Maxim Direct at 1-888-629-4642, or visit Maxim Integrated's website at www.maximintegrated.com.

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